Optical investigation of the metal-insulator transition in FeSb2

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A bstract

We present a comprehensive optical study of the narrow gap $F \in Sb_2$ semiconductor. From the optical relectivity, measured from the far infrared up to the ultraviolet spectral range, we extract the complete absorption spectrum, represented by the real part $_1(!)$ of the complex optical conductivity. With decreasing temperature below 80 K, we india progressive depletion of $_1(!)$ below $E_g = 280$ cm 1 , the semiconducting optical gap. The suppressed (D rude) spectral weight within the gap is transferred at energies $! > E_g$ and also partially piles up over a continuum of excitations extending in the spectral range between zero and E_g . Moreover, the interaction of one phonon mode with this continuum leads to an asymmetric phonon shape. Even though several analogies between $F \in Sb_2$ and $F \in Si$ were claimed and a Kondo-insulator scenario was also invoked for both systems, our data on $F \in Sb_2$ dier in several aspects from those of $F \in Si$. The relevance of our indings with respect to the Kondo insulator description will be addressed.

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I. INTRODUCTION

FeSb₂ represents an interesting case of narrow gap sem iconductor, where a band of itinerant electron states originates in the d_{xy} orbitals of the t_{2g} multiplet. The magnetic properties of FeSb₂ strongly resemble those seen in FeSi (Refs. 3 and 4). The magnetic susceptibility of FeSb₂ shows a diamagnetic to paramagnetic crossover around 100 K (Ref. 1); however in contrast to FeSi, with a very small low temperature (T) impurity tail in the diamagnetic region. The electrical transport in FeSb₂ along two axes is semiconducting, whereas the third axis exhibits a metal-semiconductor crossover at temperature T_{cr} 40 80 K, depending from the current alignment. Furthermore, the thermal expansion and heat capacity of FeSb₂ at ambient pressure agrees with a picture of a temperature induced spin state transition within the Fe t_{2g} multiplet.

A eppli and F isk⁵ proposed that the underlying physics of F eS i share comm on features with a class of rare earth compounds, known as hybridization gap sem iconductors or K ondo insulators. The analogies between F eS i and F eS b₂, pointed out above, would suggest that also F eS b₂ m ight belong to the class of d-electron based K ondo insulators. Within the K ondo insulator's scenario, one considers two narrow hybridized bands of width Winth the density of states, separated by the gap E_g . At T = 0 the electrons populate a lower hybridized band, and with the increase of T the electrons start populating the higher band, resulting in a thermally activated Pauli susceptibility⁵. This approach, successfully applied to F eS i, seems to work out for F eS b₂, as well^{1,2}. This is of particular interest because of possible relations between theoretical descriptions of d- and f-electron systems.

FeSi was also intensively investigated from the point of view of its absorption spectrum 6,7,8,9 . The charge excitation spectrum of FeSi is characterized at low temperatures by a direct gap of about 95 meV. The spectral weight, suppressed by the gap opening, is transferred to high energies. It has been long debated up to which energy the total spectral weight in FeSi is electively fully recovered 6,9 . In the data of Degiorgiet al. (Ref. 6), the spectral weight is essentially recovered at a frequency $!_c$ 4E_g , therefore without any need to invoke an integration of $_1$ (!) to very high frequencies. This conclusion is at variance with claim s^9 , suggesting a redistribution of spectral weight extending up to very high energies, even beyond the highest energy lim it of that experiment. This feature was also found to be indicative for a K ondo insulator description of FeSi (Ref. 9). As far as FeSb₂ is concerned,

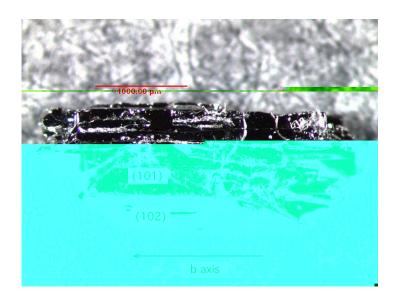


FIG. 1: $F \in Sb_2$ sample used for our optical investigations. The crystal axes, determined through the Laue spectroscopic experiment, are also shown.

a comprehensive optical study is still missing.

In addition to $F \in Si$, $F \in Sb_2$ seems to be a promising model system in order to investigate the applicability of the K ondo insulator concept with respect to the nearly itinerant magnetic semiconductor picture for 3d in termetallic compounds. The absorption spectrum of $F \in Sb_2$ should reveal important information about its intrinsic physical properties and should allow to extract the phonon spectrum as well as the relevant energy scales, like the hybridization gap. To test the applicability of the K ondo insulating concept, it is of interest to investigate the redistribution of spectral weight above and below T_{cr} in $F \in Sb_2$, addressing the issue of its conservation.

We report on our optical investigation on $F \in Sb_2$. The paper is organized as follows: we will rst characterize the specimen and describe the experiment, followed by the presentation of the optical data. The discussion will rst tackle the analysis of the phonon spectrum. Particular attention will be then devoted to the issue of the spectral weight distribution. The relevance of the K ondo insulator scenario for the description of the metal-insulator transition at $T_{\rm cr}$ in $F \in Sb_2$ will be emphasized.

II. EXPERIMENT AND RESULTS

Single crystals of FeSb, are grown from excess Sb ux, as described in Ref. 1. The crystals are cut in a rectangular shape with the long direction corresponding to the b crystalline axis. Our sample is shown in Fig. 1, which also displays the crystal orientations. We measured the optical rejectivity R (!) of our FeSb₂ specimen, over a broad spectral range (30 to 10^5 cm 1) and as a function of temperature. Light was polarized along the baxis (E k b) and along the direction perpendicular (E? b) to the baxis within the (102) surface (Fig. 1). The real part 1 (!) of the optical conductivity was obtained through K ram ers-K ronig (KK) transform ation 10,11 of R (!). To this end, we applied standard high-frequency extrapolations ! $^{\rm s}$ (with 2 < s < 4) in order to extend the data set above 10^5 cm $^{\rm 1}$ into the R (!) electronic continuum. Below 30 cm⁻¹, R (!) was extrapolated towards zero frequency either by using the Hagen-Rubens (HR) law R (!)=1 $2^p \frac{p}{(!=d_c)}$ for re-ectivity data at T > T_{cr}, displaying a metallic behavior, or by imposing R (! < $!_{m \text{ in}}$)= R ($!_{m \text{ in}}$ = 30 cm $^{-1}$) for data in the insulating state at T < T_{cr} . Nevertheless, the overall behaviour of $_{1}$ (!) is not a ected by the details of these extrapolations. Details pertaining to the experiment can be found in Refs. 10 and 11.

Figure 2 presents R (!) and $_1$ (!) in the far-infrared (FIR) spectral range at 10 and 150 K for both polarizations of light, while the insets display the spectra at 150 K for both quantities over the whole measured spectral range (the reader should pay attention to the use of the logarithm ic energy scale in the insets). R (!) at 150 K displays a metallic behavior for both polarization directions, with a plasm a edge onset at 3000 cm^{-1} (inset of Fig. 2a). The anisotropy in R (!) is not very pronounced at 150 K, even though the E? bre ectivity is depleted with respect to R (!) along the baxis in the spectral range between 300 and 1000 cm^{-1} . With decreasing T and for both polarizations, R (!) attens in the far infrared range (Fig. 2a), an indication for a metal to insulator (M I) transition. The enhancement of phonon-like structures, especially for E? b, is also observed at 10 K (i.e., in the insulating state). R (!) at 150 and 10 K merge together at $350 \text{ and } 450 \text{ cm}^{-1}$, for light polarization E k b and E? b, respectively. The anisotropic behavior in the optical response between the two polarization directions becomes more evident at low temperatures. In the far infrared range, R (!) at 10 K along the baxis is approximately 10% higher with respect to the other crystallographic axis. Furtherm ore, the anisotropic electrodynamic response clearly shows

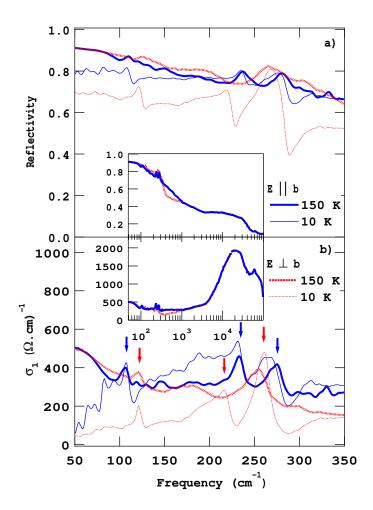


FIG. 2: (color online) a) 0 ptical re-ectivity R (!) and b) realpart $_1$ (!) of the optical conductivity of FeSb₂ in the far infrared range, with light polarized along the b crystallographic axis (E k b) and perpendicular to the b axis (E? b) at 150 and 10 K. Insets: R (!) and $_1$ (!) for frequencies up to 10^5 cm 1 (the reader should note the use of the logarithm ic energy scale). Blue and red arrows indicate the low temperature phonon modes for E k b and E? b, respectively.

the presence of di erent phonon features along the two crystallographic directions.

The realpart 1(!) of the optical conductivity, as extracted from the KK transform ations, is shown in Fig. 2b. At 150 K (inset of Fig. 2b), one can easily recognize the presence of a D rude m etallic term at low frequencies, for both polarization directions, as well as the strong absorption at 20000 cm⁻¹ due to an electronic interband transition. With decreasing temperature, the D rude term vanishes along both directions (main panel of Fig. 2b). Furthermore, for E k b we can clearly distinguish phonon modes at 107, 231, 270

cm 1 (blue arrows in Fig. 2b); the latter one seems to be made up by two distinct modes, yet not completely resolved. On the other hand, $_{1}$ (!) for E ? b displays phonon features at $_{1}$ 122, 217, 260 cm $_{1}$ (red arrows in Fig. 2b). The mode at 217 cm $_{1}$ is clearly present at low temperatures only.

III. DISCUSSION

A. The tting procedure

TABLE I: $F \in Sb_2 - E$ k b. Lorentz-D rude t param eters. All param eters are given in units of [cm 1], with the exception of $_1$ which is unit-less.

Param eters	10 K	30 K	50 K	70 K	100 K	150 K
1	1	1	1	1	1	1
! pD	-	-	-	-	1400	1900
D	-	_	_	-	75	85
! p1	580	510	480	480	300	300
! 01	106.4	107.5	107.5	107.5	107.5	106.3
1	13	12	10.5	10.5	10.5	12
! p2	650	650	650	680	590	560
! 02	231	231	231	231	232	232.9
2	15	15.5	15.5	15.5	15.5	15
! p3	635	600	615	520	520	455
! 03	257	257	256.5	258.3	258.3	264
3	25	25	25	25	25	25
! p4	655	655	650	715	630	625
! ₀₄	271	272.5	273	272	274	276
4	25	23	20	22	22	25

The optical conductivity is analyzed within the framework of the phenomenological Lorentz-D $\operatorname{rude}^{10,11}$ model extended to the Fano approach $\operatorname{^{12,13,14}}$ in order to account for the asymmetric shape in the phonon modes. The D rude metallic behavior is defined by the

TABLE II: $F \in Sb_2 - E$? b. Lorentz-D rude and Fano t parameters. All parameters are given in units of [cm 1], with the exception of $_1$ and q which is unit-less.

Param eters	10 K	30 K	50 K	70 K	100 K	150 K
1	1	1	1	1	1	1
! pD	_	_	_	900	1484.5	2100
D	_	_	_	80	112.8	130
! p1	365	350	335	275	225	230
! 01	121	121	122.5	122	123	121
1	11.5	12	12	9	10	12
! p2	420	410	400	420	_	-
! ₀₂	216	217	219	219.5	_	-
2	13	13	13	18	_	_
! p3	776.1	746.3	724.4	722.6	777	800
! ₀₃	261.4	262.5	263.8	263.4	261.4	254.0
3	21.1	19.5	19.6	20.3	0.88	40.0
q ₃	-6.41	-6.87	−7 . 67	-7 . 91	-16	-16

formula:

$$_{D} (!) = \frac{!_{pD}^{2}}{4_{D}} \frac{1}{1 \quad i! = D};$$
 (1)

where the plasm a frequency is $!_{pD} = \frac{p}{4 \text{ N e}^2 = m}$ and $_D$ is the scattering rate. Besides the D rude term, we add four and two Lorentz harmonic oscillators for E k b and E? b, respectively. The contribution due to a Lorentz harmonic oscillator is:

$$_{\text{Lorentz}}^{j}(!) = \frac{!_{pj}^{2}}{4} \frac{!}{i(!_{0j}^{2} !^{2}) + !_{j}};$$
(2)

where $!_{0j}$ is the resonance frequency, $_j$ the damping and $!_{pj}$ the strength of the j-m ode. For E ? b, there is additionally a third contribution, described by a Fano lineshape for the asymmetric mode at 260 cm⁻¹. The contribution due to the Fano mode is given by the equation^{13,14}:

$$\int_{\text{F ano}} (!) = i \int_{0j} \frac{(q_j + i)^2}{x_j(!) + i};$$
(3)

with

$$x_{j}(!) = \frac{!_{0j}^{2} \quad !_{2}^{2}}{j!}; \text{ and } _{0j} = \frac{!_{pj}^{2}}{jq_{j}^{2}};$$
 (4)

where the same notation as in eq. (2) has been used. The dimensionless q_j Fano parameter is a measure of the degree of asymmetry of the peak at $!_{0j}$ (for jqj! 1 a Lorentzian lineshape is recovered). The Lorentz and Fano contributions describe the modes, marked by arrows in Fig. 2b, which clearly develop at low temperatures.

Table I and II sum marize the tem perature dependence of the parameters employed in our ts. We immediately observe that with decreasing temperature, the plasma frequency decreases for both polarizations. From our ts we can dene two intervals of temperatures for the MI transition, $T_{MI}^{kb} = 70\text{--}100 \text{ K}$ and $T_{MI}^{?b} = 50\text{--}70 \text{ K}$, as the range of temperatures at which the D rude term vanishes. Our T_{MI} values are in good agreement with T_{CI} , which denes the metal-sem iconducting crossover in the (I) transport data 1. A nother interesting aspect in the infrared spectra of FeSb₂ is the quite largemode strength of the infrared active phonons. Particularly, the phonons at 1_{02} , 1_{03} and 1_{04} for E k b and the Fanomode at 1_{03} for E? bexhibit at low temperatures mode strengths between 600 and 800 cm. This could suggest highly ionic character for FeSb₂. In this respect, FeSb₂ shares a common property with FeSi (Ref. 9). Schlesinger et al. also pointed out that strong phonons have been observed in prototype heavy ferm ions systems and cuprates, as well⁹.

While the temperature dependence of the phonon modes and in general of $_1$ (!) in the far infrared (FIR) spectral range will be extensively discussed below, we anticipate here that the proposed tonly partially reproduces the measured spectra. Indeed, there is a broad continuum of low frequency excitations in the FIR spectral range and at low temperatures for both polarizations, which is not encountered by this t procedure.

B. Lattice Dynamics

1. Factor group analysis

FeSb₂ crystallizes in the marcasyte-type structure with two formula units per unit cell. FeSb₂ is made up of FeSb₆ octahedra which form edge sharing chains along the caxis. The space group is the centrosymmetric P nnm orthorhombic group¹, for which we report the factor group analysis in Table III. By using the correlation method¹⁵, and after subtracting the acoustic modes, we not for the total irreducible representations:

$$P_{nnm} = A_q + 2A_u + B_{1q} + B_{1u} + 2B_{2q} + 3B_{2u} + 2B_{3q} + 3B_{3u}$$
: (5)

Nom al	N um ber	of	m odes		
m odes	Total	A coustic	0 ptical	Ram an	IR
Ag	1		1	aa, bb, ∞	
B _{1g}	1		1	ab	
B _{2g}	2		2	ac	
B 3g	2		2	bc	
A_u	2		2		
B _{1u}	2	1	1		E//c
B _{2u}	4	1	3		E//b
B _{3u}	4	1	3		E//a

TABLE III: Norm almodes analysis of FeSb for the Pnnm symmetry group.

By comparing our data with the theoretical calculation for the number of infrared active phonon modes along the baxis direction (E kb), one can notice that our optical measurement suggests the presence of four instead of three phonon modes. Nevertheless, the resonance frequencies of the modes at 257 and 271 cm⁻¹ are quite close to each other. Therefore, optical spectra may reveal a slightly lower symmetry for $F \in Sb_2$ with respect to the one predicted by the P nnm group¹.

A long the direction perpendicular to the baxis (E? b) three phonon modes are present at low temperature, while only two of them are still observable above 50 K. If one assumes

the P nnm group symmetry for $F \in Sb_2$, our spectra would in ply that the axis perpendicular to b in our experiment corresponds to the crystallographic direction a. On the other hand, the disappearance of the phonon mode at 216 cm⁻¹ at high temperatures might suggest a phase transition into a state, where this specic phonon is silent and not infrared active. Nevertheless, no structural changes have been found so far in $F \in Sb_2$ down to 10 K (Ref. 2).

2. Fano analysis

A blow up of the spectral range pertinent to the asym metric mode at 260 cm⁻¹ for E? b at 10 K is displayed in Fig. 3a. It is easily recognized that the Fano mode is more appropriate than a simple Lorentz oscillator in order to reproduce the overall shape of this mode. The temperature dependence of the thing parameters for this peculiar mode is displayed in Fig. 3b-e. The oscillator strength is associated to the elective transverse charge and has a non-trivial temperature dependence (Fig. 3b) since it is decreases with increasing T, passes through a minimum between 50 and 70 K (i.e. in correspondence with the MI transition temperature) and then increases again.

A similar trend is also found for the resonance frequency $!_{03}$ (Fig. 3c), which slowly increases with increasing T before displaying a well dened softening at high temperatures. X-ray direction studies² have established that the Fe Sb Fe bond angle, associated with the edge sharing octahedra along the caxis, increases above 100 K. The T-dependence of the Fe Sb Fe angle behaves rather closely to the behavior of $!_{03}$. These observations, together with the appearance at low T of the mode at 216 cm⁻¹, are clear evidence for a structural distortion accompanying the MI transition.

The damping factor $_3$ (Fig. 3d) increases above $T_{MI}^{?b}$. Since $_1$ = , this indicates a two times higher phonon lifetime in the low $_3$ insulating state. Such a strong correlation between the onset of the insulating state and the loss of phononic relaxational channels also suggests the presence of a coupling mechanism between the electronic degrees of freedom and the lattice vibrations, as already claimed for FeSi (Ref. 16).

Finally, Fig. 3e displays the T-dependence of the dimensionless Fano parameter q. At high T, jqj is of the order of 16. Such a high q-value in plies that above 100 K an asymmetric phonon lineshape can be hardly recognized; a Lorentz harm onic oscillator would tequally well this mode. On the other hand, q takes values between -6.4 and -7.9 below $T_{\rm M}^{\rm 2.5}$, indi-

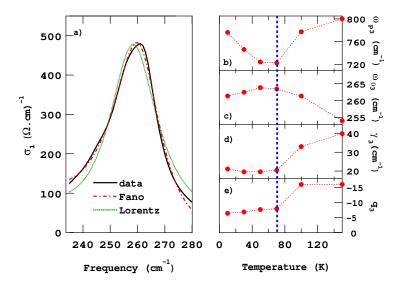


FIG. 3: (color online) a) B low-up of $_1$ (!) around the mode at 260 cm 1 at 10 K and for E? b. The ts of this mode with either a Lorentz harm onic oscillator or a Fano lineshape are shown for comparison. b) Temperature dependence of the oscillator strength ! $_{p3}$, c) resonance frequency ! $_{03}$, d) scattering rate $_3$, and e) asymmetry factor $_3$ of the mode at 260 cm 1 within the Fano-like t. The blue dashed line indicates the upper lim it of T $_{\rm M}^{\, 2}$ i.

cating a sizable asymmetric lineshape. The presence of Fano lineshapes is predicted when a discrete lattice vibration is degenerate with states belonging to a continuum which may be of electronic or magnetic nature 12 . Interestingly, Fano lineshapes have been also observed in the infrared spectra of FeSi (Ref. 16). In that case, the asymmetry was ascribed to the interaction of the phonon mode with an electronic resonance peaked in the mid-infrared range, i.e. above the phonon resonance frequency. However, for FeSb₂ the sign of q(<0) is consistent with the picture of the phonon at 260 cm^{-1} coupled to an energy scale which is lower than the phonon resonance frequency. The forthcoming analysis of the spectral weight distribution in the absorption spectrum of FeSb₂ will shed more light on this low energy scale.

C. Spectral weight analysis

The $_1$ (!) spectra at 10 K present for both polarizations a deep m inim um at about 280 cm 1 , which coincides with the onset of a broad and tem perature independent tail, ascribed to the incoherent electronic contribution. We call such an energy, de ning the onset of the interband transitions, E_g . E_g 280 cm 1 is therefore an appropriate estimation for the insulating optical gap in FeSb₂. The value of E_g is sizably larger with respect to its estimation based on the activated behaviour of the resistivity, which indicates (a;c) 200 cm 1 , and (b) 170 cm 1 (Ref. 1). Similarly to the case of FeSi (Ref. 8), this discrepancy in the gap value among dierent experiments could be reconciled by assuming a small indirect energy gap for the transport properties and a larger direct gap for the optical response. On the other hand and at variance with FeSi (Ref. 16), E_g does not display any temperature dependence up to the temperature ($I_{\rm M}$ I), at which the M I transition is observed.

By integrating the optical conductivity (i.e., $\begin{bmatrix} R_{!c} \\ 0 \end{bmatrix}$ rude (!)d!), we can achieve the spectralweight encountered in the absorption spectrum over a frequency interval between zero and $!_c$. Because of the tem perature dependence of $_1$ (!) (Fig. 2b), there is an obvious redistribution of the spectral weight from low to high frequencies in our spectra. A sum rule 10,11 requires that the integrated area under 1 (!) must be unchanged at any tem perature; therefore predicting the conservation of the spectral weight. In a conventional semiconducting scenario, the T-induced M I transition is simply due to the therm alexcitation of charge carriers through the energy gap Eq. From an optical point of view, one would therefore expect that by low ering the tem perature through $T_g = E_g/k_B$ the D rude term progressively vanishes while the spectral weight lost at ! < E_g redistributes just above and close to E_g . Such a picture is inadequate for $F \in Sb_2$. We not that the overall depletion of $_1$ (!) at 10 K leads to a rem oval of spectral weight at low frequencies, which mostly (i.e., 90%) piles up in the spectral range between E_q and 3000 cm $^{-1}$. However, a full recovery of the spectral weight only occurs when integrating $_1$ (!) up to 1 eV . The observation, that one needs to go to unusually high frequency to satisfy the conduction sum rule, m ight suggest, sim ilarly to FeSi⁹, that the physics of FeSb₂ involves an energy scale much larger than the gap energy ${\bf E}_{\,{f q}}$. The transfer of spectral weight in spectroscopies of correlated electron systems has been discussed in the fram ework of the periodic Anderson model for the situation pertinent to

the K ondo insulators 17.

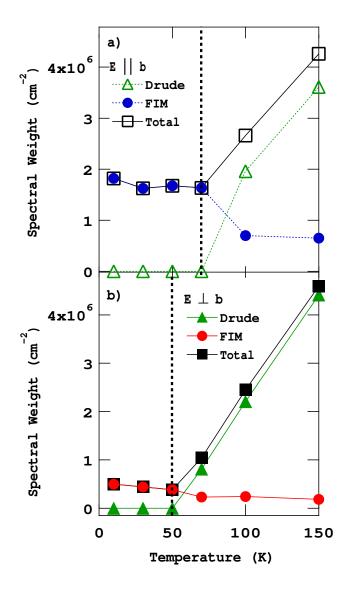


FIG. 4: (color online) Tem perature dependence of the spectral weight encountered in $_1$ (!) at ! < E $_g$ for E k b (a) and E ? b (b). The black squares represent the integrals of $_1$ (!) up to 280 cm 1 after having subtracted the t to the phonon modes. The green triangles represent the spectral weight of the metallic D rude term. The blue and red circles represent the spectral weight (A) of the broad infrared mode (FIM) for E k b and E? b, respectively.

We can now calculate the total spectral weight encountered in $_1$ (!) of FeSb₂ at frequencies lower than E_g . To do so we have subtracted the phonons' contribution. The temperature dependence of this latter quantity is plotted in Fig. 4 for both polarization

directions (open and led black squares for E k b and E? b, respectively). We remark that at T > $T_{\rm M~I}$ a fraction of the total spectral weight below $E_{\rm g}$ is due to a background of weight distributed over an interval of energies extending from 0 up to E_q . We associate such a background of spectral weight to the presence of a continuum of low lying excitations. This continuum of excitations de nes a broad far infrared mode (FIM). The total spectral weight up to E_q decreases with decreasing temperature down to $T_{M\ I}$ (Fig. 4). Below $T_{M\ I}$, som e residual spectral weight (which can not be of vibrational origin) survives inside of the gap. As demonstrated in Fig. 4, the spectral weight of the D rude term disappears below T_{M} . The rem oved D rude weight is transferred at high energies and partially piles up in the spectral range covered by FIM. The size of this FIM term increases indeed with decreasing tem perature, as shown in Fig. 4. The continuum of excitations, de ning FIM, is better highlighted in the insets of Fig. 5. The red and blue area for for E k b and E? b, respectively, represent the spectral weight encountered in FIM (for the data at 10 K). Such areas (A) are calculated by subtracting the spectral weight encountered in the D rude-Lorentz t from the total spectral weight underneath the measured $_1$ (!) curve. Figure 5 displays then the tem perature dependence of A, normalized by its value at 10 K (Ref. 18). At approxim ately $T_{M\ I}$ the spectral weight associated to FIM suddenly increases and the T-dependence A vaguely m im ics the behaviour of an order param eter.

The temperature dependence of A seems to shape the intrinsic electronic properties of $F \in Sb_2$. In fact, the presence of such a (FIM) continuum in plies that several localized states are present at low temperatures between the valence and the conduction band. Above $T_{M\ I}$ those states, generating $F \setminus M$, are thermally occupied. Envisaging an overlapping of these states, a coherent electronic transport can then develop. In this context, it is not surprising that $T_{M\ I}$ is lower than E_g . Furthermore, the presence of this continuum of excitations supplies a natural explanation for the Fano behavior of the mode at $!_{03}$ = 260 cm $^{-1}$ for $E \in P$. As anticipated above, the negative sign of the q Fano parameter in plies an interaction of the mode at $!_{03}$ with a continuum covering an energy spectral range located below $!_{03}$. Such a continuum of excitations is precisely provided by $F \setminus M$. As comparison, we note that in the case of $F \in Si$, where no evidence for an equivalent $F \setminus M$ feature was found, the asymmetry of the phonons was on the contrary ascribed to the red-shift of the gap edge 16 . The gap edge in $F \in Sb_2$ is temperature independent. Therefore, this excludes any possibility for a temperature dependent coupling between the phonon modes and mid infrared excitations.

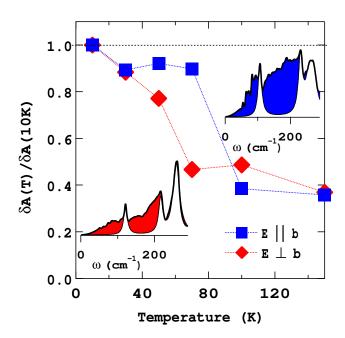


FIG. 5: (color online) Tem perature dependence of the normalized spectral weight (A) of FIM. Insets show the area A (blue and red for E k b and E? b, respectively) at low tem perature, encountering the spectral weight of FIM (see text).

IV. CONCLUSION

The electrodynam ic response of $F \in Sb_2$ is characterized by a metal-insulator transition occurring at T < 70 K, and opening of a gap $E_g = 280$ cm $^{-1}$. W ith decreasing tem perature there is a depletion of $_1$ (!) signalling the rem ovalof spectral weight, which is shifted to high energies up to 1 eV. Furtherm ore, we have observed that the suppressed D rude weight with decreasing tem perature (i.e., at $T < T_{cr}$) partially piles up in the broad far infrared mode (FIM), which we have ascribed to a continuum of excitations. An ordinary semiconductor picture cannot account for the charge dynamic of $F \in Sb_2$. While some features in the optical response may be compatible with a K ondo insulator scenario, it remains to be seen how the presence of the continuum of excitations in the far infrared and at $! < E_g$ might eventually be consistent with such a description. Our indings challenge indeed the theoretical treatment of the K ondo insulators within the framework of the periodic Anderson model¹⁷.

A cknow ledgm ents

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